Amendments to the Specification

Please replace the paragraph starting at page 10, line 26 with the following amended version of that paragraph:

The circuitry of integrated circuit 30 (e.g., the digital circuits on circuit 30) typically include a number of transistors such as ~~transistor~~ transistors 32 and/or 33. These transistors may have a source 36 at a first terminal, a drain 38 at a second terminal, and a controlling gate electrode 34 at a third terminal. Some of the other circuitry on integrated circuit 20 (called gate control circuitry 30 in FIG. 1 and called control circuitry or control circuits elsewhere) may be used to control transistors such as ~~transistor~~ transistors 32 and 33. The gates of many transistors on circuit 20 are either supplied with a high voltage (e.g., a logic high level) such as Vcc (e.g., 1.2 volts) or a low voltage (e.g., a logic low level) such as Vss (e.g., 0 volts).

Please replace the paragraph starting at page 11, line 9 with the following amended version of that paragraph:

When a high signal is applied to a given transistor, an inversion layer is formed beneath gate 34 which turns the transistor on. This allows signals to pass through the transistor. When a low ~~signals~~ signal is applied

to transistor 32 or 33, the transistor is turned off. Thus, many of the transistors on circuit 20 act as switches, which either block signals or let signals pass between their source and drain terminals, depending on the state of the control signal applied to their gate control terminals 34.

Please replace the paragraph starting at page 13, line 9 with the following amended version of that paragraph:

The transistors on circuit 20 may be fabricated so that they have different threshold voltages. For example, some transistors may be configured to have relatively higher threshold voltages (e.g., $V_{TH}$ = 0.4 volts), others may be configured to have moderate threshold voltages (e.g., 0.3 volts), and still others may be configured to have relatively lower threshold voltages (e.g., $V_{TH}'$ = 0.2 volts). The decision as to which transistors to provide with which threshold voltages depends on the intended use of the transistor and its circuit environment.

Please replace the paragraph starting at page 14, line 3 with the following amended version of that paragraph:

The use of the reverse bias voltage Vss' to turn off the transistors of circuit 20 reduces leakage current the most for low-threshold transistors, reduces leakage somewhat

for medium-threshold transistors, and reduces leakage to a lesser extent for high-threshold transistors. As a result, it may be particularly advantageous to use the reverse bias voltage Vss' to turn off the transistors with the low (or even medium) thresholds. Using the reverse bias voltage Vss' to turn off these transistors has the greatest impact in reducing the standby power consumption (on a per-transistor basis). Because there is overhead associated with providing charge pump circuitry 28 and gate control circuitry 30 to allow transistors [[34]] 32 to be turned off with reverse bias signal Vss', it may be desirable to turn off some of the transistors (e.g., some or all of the high-voltage-threshold transistors 33) using Vss and to turn off other transistors (e.g., some or all of the low-voltage-threshold transistors 32) using Vss'.